

Title (en)
SILICON NOZZLE STRUCTURES AND METHOD OF MANUFACTURE

Publication
EP 0178596 B1 19910116 (EN)

Application
EP 85112882 A 19851011

Priority
US 66100584 A 19841015

Abstract (en)
[origin: EP0178596A2] A nozzle structure in a crystallographically oriented, monocrystalline silicon includes a pyramidal opening (11) anisotropically etched from the entrance side of the nozzle and truncated in a membrane (12) having a smaller cross-section than the initial cross-section of the entrance opening. The membrane (12) has extending therethrough a pyramidal opening (13) etched anisotropically from the exit side. The vertical axes of both openings are substantially concentric.

IPC 1-7
B05B 1/00; B41J 2/135; B41J 2/16

IPC 8 full level
B05B 17/04 (2006.01); **B41J 2/135** (2006.01); **B41J 2/16** (2006.01)

CPC (source: EP KR)
B41J 2/005 (2013.01 - KR); **B41J 2/162** (2013.01 - EP); **B41J 2/1629** (2013.01 - EP); **B41J 2/1631** (2013.01 - EP); **B41J 2/1632** (2013.01 - EP); **B41J 2/1642** (2013.01 - EP)

Cited by
EP0317300A3; EP0921004A3; EP1170128A1; US6120131A; EP0578130A1; EP0921002A3; US6463656B1; US6485132B1; US6323456B1; US6375858B1; US6863375B2

Designated contracting state (EPC)
BE DE FR GB IT NL

DOCDB simple family (publication)
EP 0178596 A2 19860423; EP 0178596 A3 19870916; EP 0178596 B1 19910116; EP 0178596 B2 19940601; AU 4819085 A 19860424; AU 582581 B2 19890406; CA 1237020 A 19880524; DE 3581355 D1 19910221; ES 296483 U 19871016; ES 296483 Y 19880416; ES 547845 A0 19870816; ES 8707144 A1 19870816; JP S6198558 A 19860516; KR 860003109 A 19860519; KR 930009109 B1 19930923

DOCDB simple family (application)
EP 85112882 A 19851011; AU 4819085 A 19851002; CA 477672 A 19850327; DE 3581355 T 19851011; ES 296483 U 19870413; ES 547845 A 19851014; JP 22795685 A 19851015; KR 850007532 A 19851014